



Powerex, Inc., 200 E. Hillis Street, Youngwood, Pennsylvania 15697-1800 (724) 925-7272

CM150DUS-12F
Trench Gate Design Dual IGBTMOD™
 150 Amperes/600 Volts

Thermal and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

| Characteristics | Symbol | Test Conditions | Min. | Typ. | Max. | Units |
|--------------------------------------|----------------|--|------|------|--------|--------------------|
| Thermal Resistance, Junction to Case | $R_{th(j-c)Q}$ | Per IGBT 1/2 Module, T_c Reference Point per Outline Drawing | – | | 0.24 | $^\circ\text{C/W}$ |
| Thermal Resistance, Junction to Case | $R_{th(j-c)D}$ | Per FWDi 1/2 Module, T_c Reference Point per Outline Drawing | – | – | 0.47 | $^\circ\text{C/W}$ |
| Thermal Resistance, Junction to Case | $R_{th(j-c)Q}$ | Per IGBT 1/2 Module, T_c Reference Point Under Chip | – | – | 0.19** | $^\circ\text{C/W}$ |
| Contact Thermal Resistance | $R_{th(c-f)}$ | Per Module, Thermal Grease Applied | – | 0.07 | – | $^\circ\text{C/W}$ |
| External Gate Resistance | R_G | | 4.2 | – | 42 | Ω |

** If you use this value, $R_{th(f-a)}$ should be measured just under the chips.

